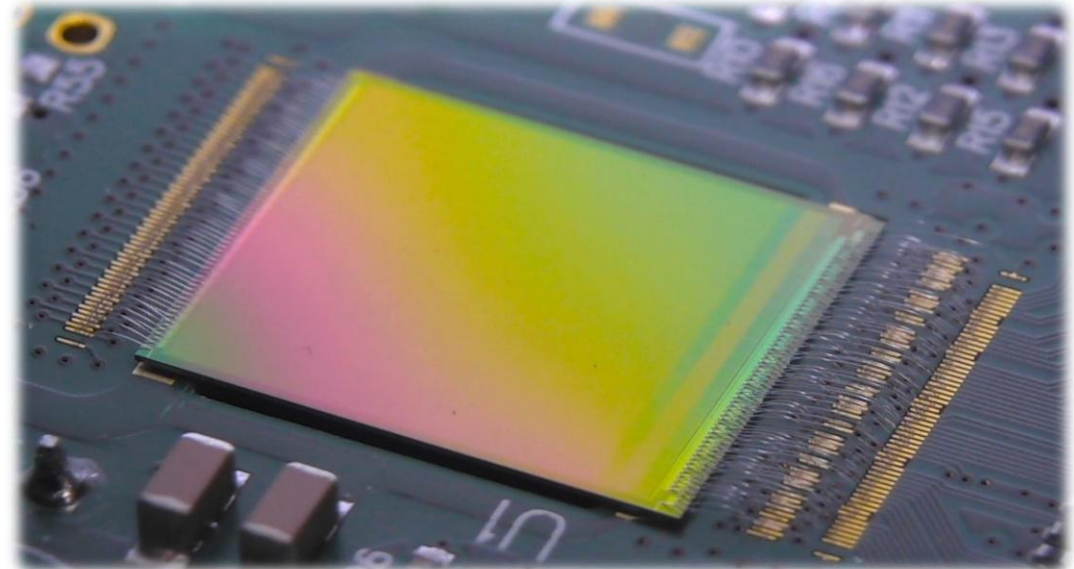


The ARCADIA Fully Depleted MAPS: laboratory characterization and particle tracking performance

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C. Pantouvakis^(b,c), C. Pena^(e), M. Rignanese^(b,c), N. Salvador^(h), R. Turrisi^(b), J. Wyss^(d,b),
Y. Takahashi^(f), S. Xie^(e), T. Zenger^(e), A. Zingaretti^(b,c), I. Zoi^(e)

- a. University of Padova, Centro di ateneo di Studi e Attività Spaziali CISAS Giuseppe Colombo, Padova, Italy
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- c. University of Padova, Department of Physics and Astronomy G. Galilei, Padova, Italy
- d. University of Cassino and Southern Lazio, DICEM, Cassino, Italy
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- f. A. Alikhanyan National Science Laboratory, Yerevan, Armenia
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Advanced Readout CMOS Architectures with Depleted Integrated sensor Arrays



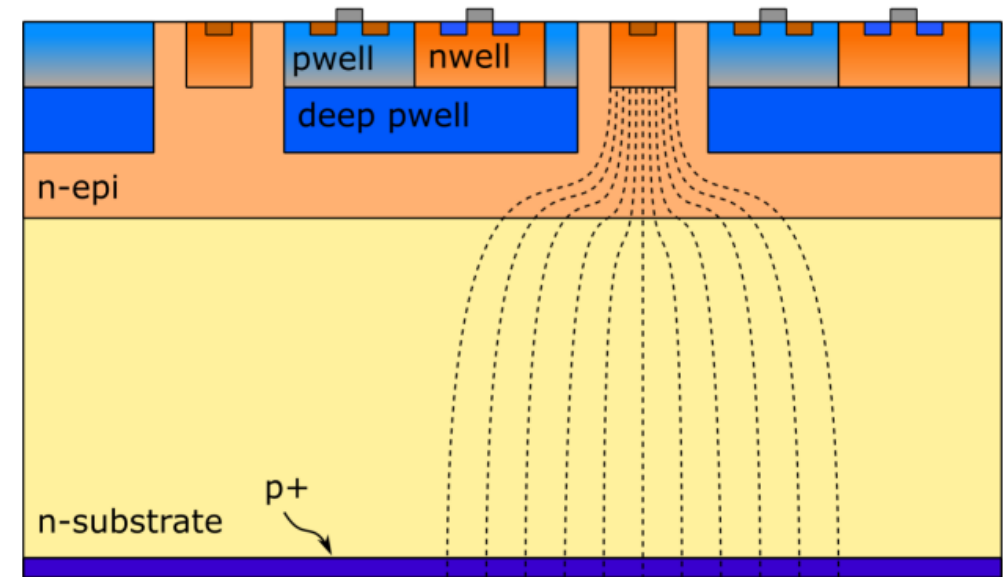
R&D project, funded by INFN CSN5, on the **development of thick FD-MAPS** in a customized **LFoundry 110 nm CIS** process in view of the next generation of HEP experiments, e.g. FCC-ee, space experiments and X-ray detection

Sensor

- n-type high resistivity active region (up to 500 μm)
- n-epi layer to control the potential below the deep pwell
- sensing electrodes can be biased at low voltage ($< 1\text{V}$)
- backside p^+ implantation: depletion from back to top

Scalable readout architecture with ultra-low power capability $\text{O}(10 \text{ mW}/\text{cm}^2)$

See M. Rolo «*Status and plans of the ARCADIA project and LFoundry 110 nm*»



M. Rolo, VERTEX2023, <https://agenda.infn.it/event/35597/contributions/211639/>
L. Pancheri et al, 2019 JINST 14 C06016, DOI: [10.1088/1748-0221/14/06/C06016](https://doi.org/10.1088/1748-0221/14/06/C06016)

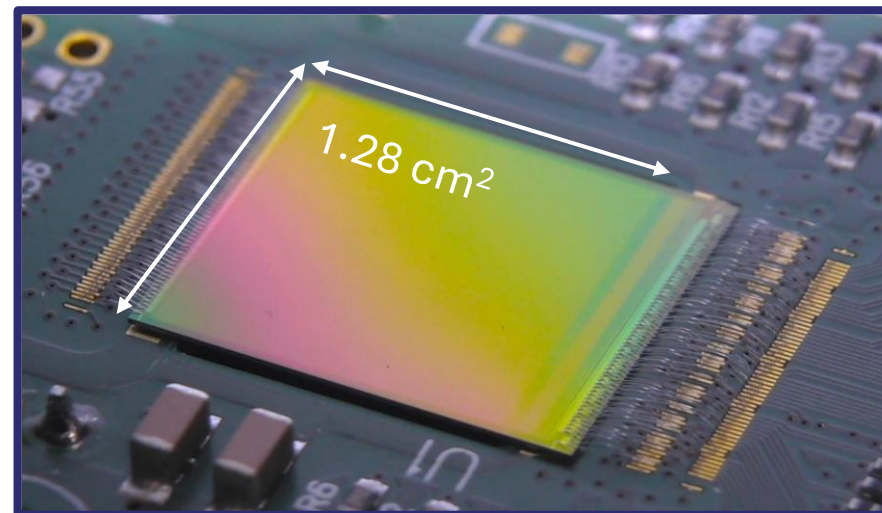


Full chip demonstrator MD3

Pixel array	512 × 512 pixels
Pixel pitch	25 μm
Readout	Data-driven binary
Power consumption	< 30 mW/cm ² (down to 10 mW/cm ² in low rate mode)
Active thickness	50, 100, 200 μm
Rate capability	100 MHz /cm ²

Applications

Particle tracking – Space - Medical



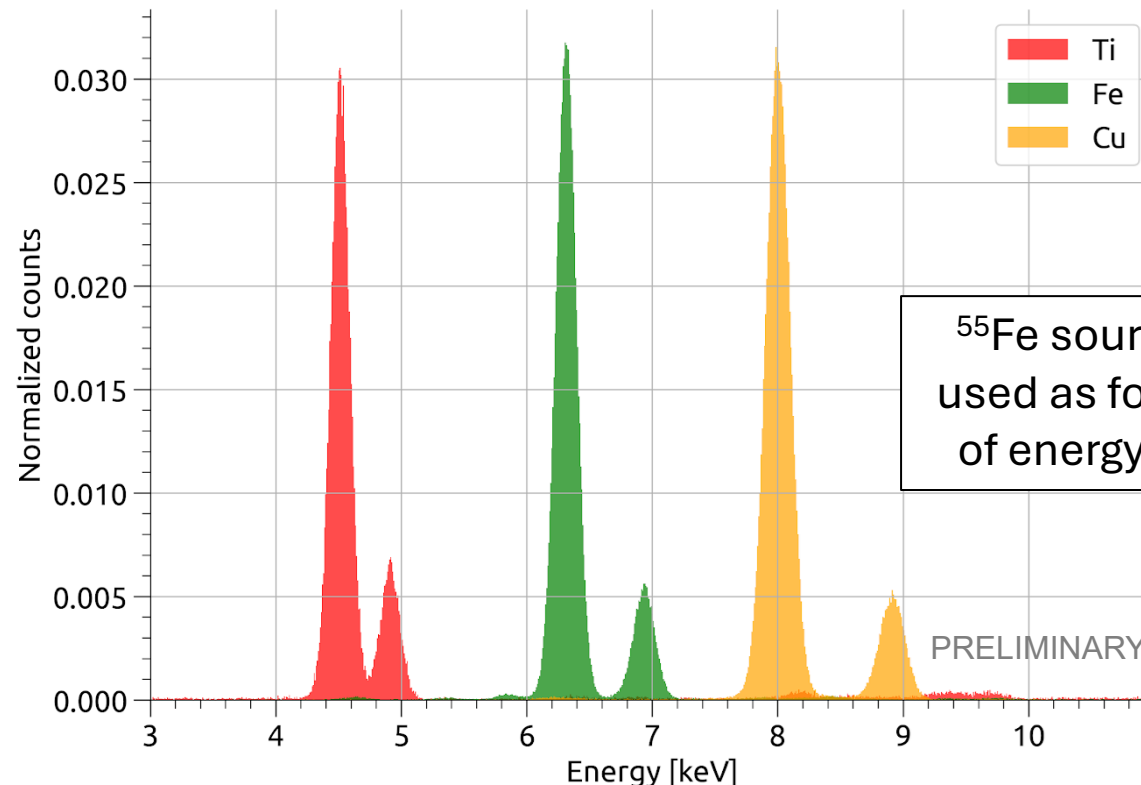
More details in: M. Rolo et al., ARCADIA fully depleted CMOS MAPS development with LFoundry 110 nm,
DOI:10.3389/fsens.2025.1603755 ISSN=2673-5067

MD3 characterization: fluorescence

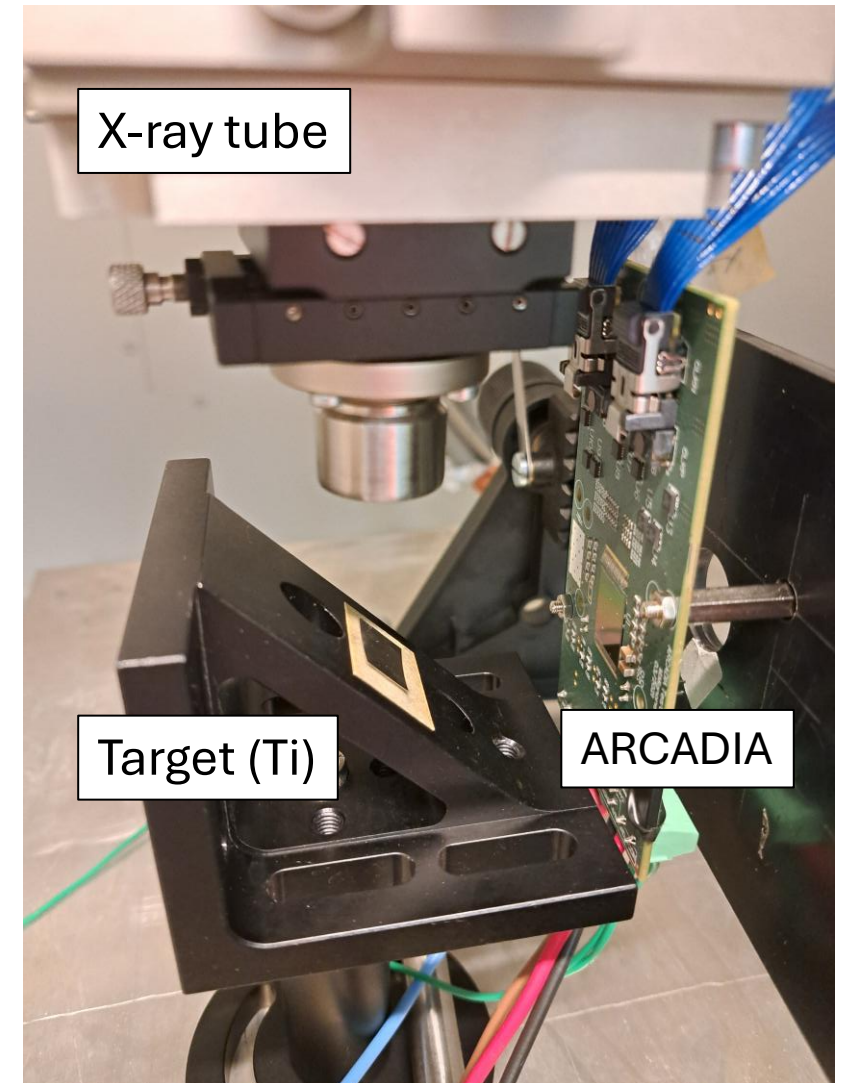
Fluorescence is a source of very monochromatic X-ray.
It can be exploited to calibrate the sensor.

Setup:

- X-ray tube with Tungsten anode used at 40kV and 50 mA
- Target of different materials at 45°
- 16×16 pixel array tested

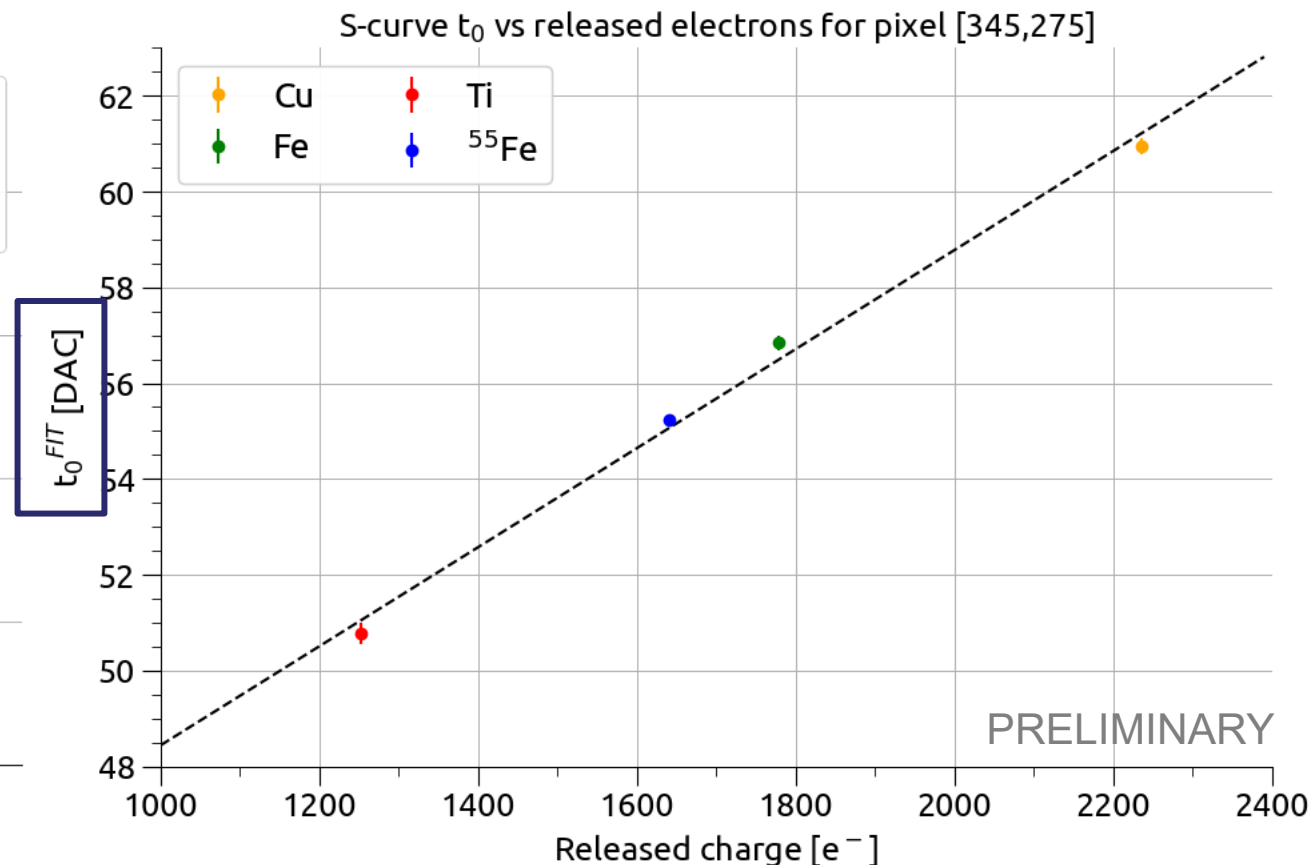
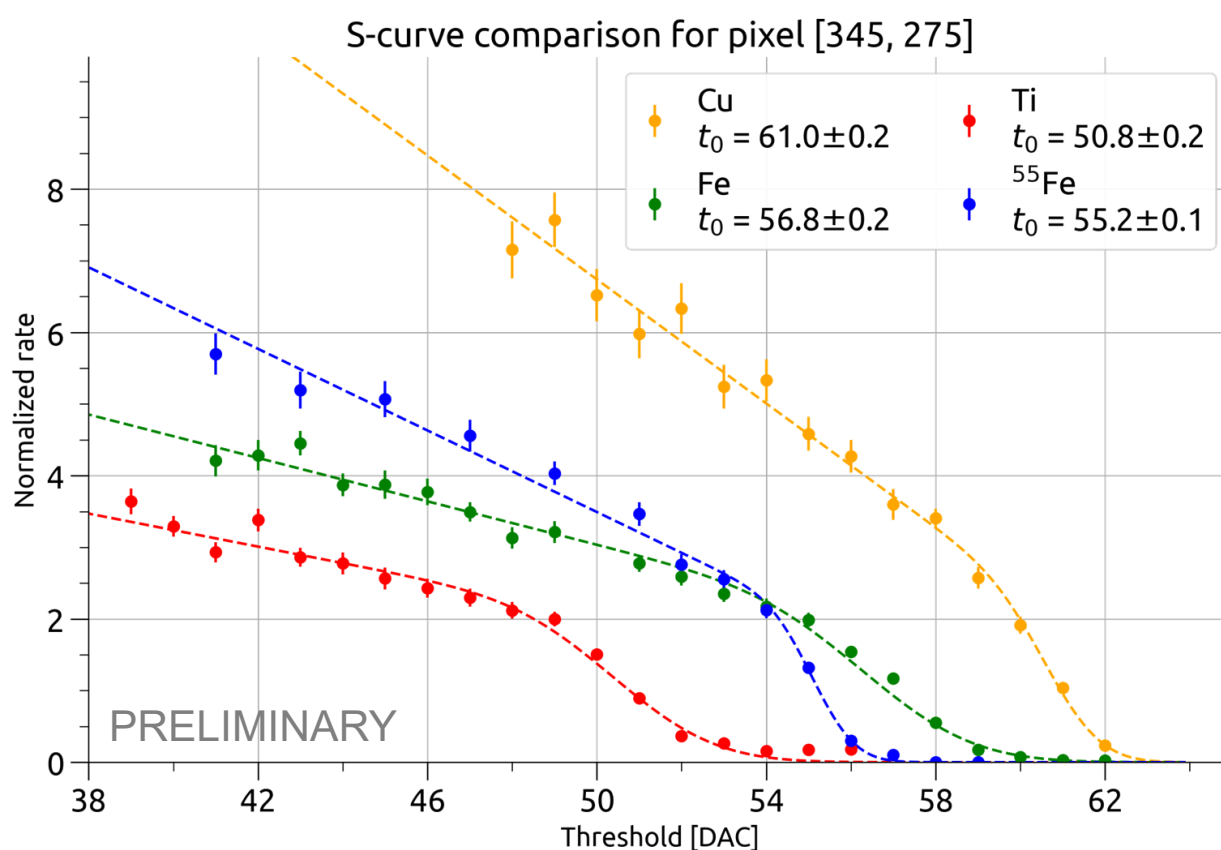


^{55}Fe source is also
used as fourth value
of energy (5.9 keV)



Spectra acquired with Amptek XR-100CR detector

Comparison of s-curve for all targets from fluorescence and from ^{55}Fe source.
The rate is normalized to have the s-curve middle point (t_0) at rate equals to 1.

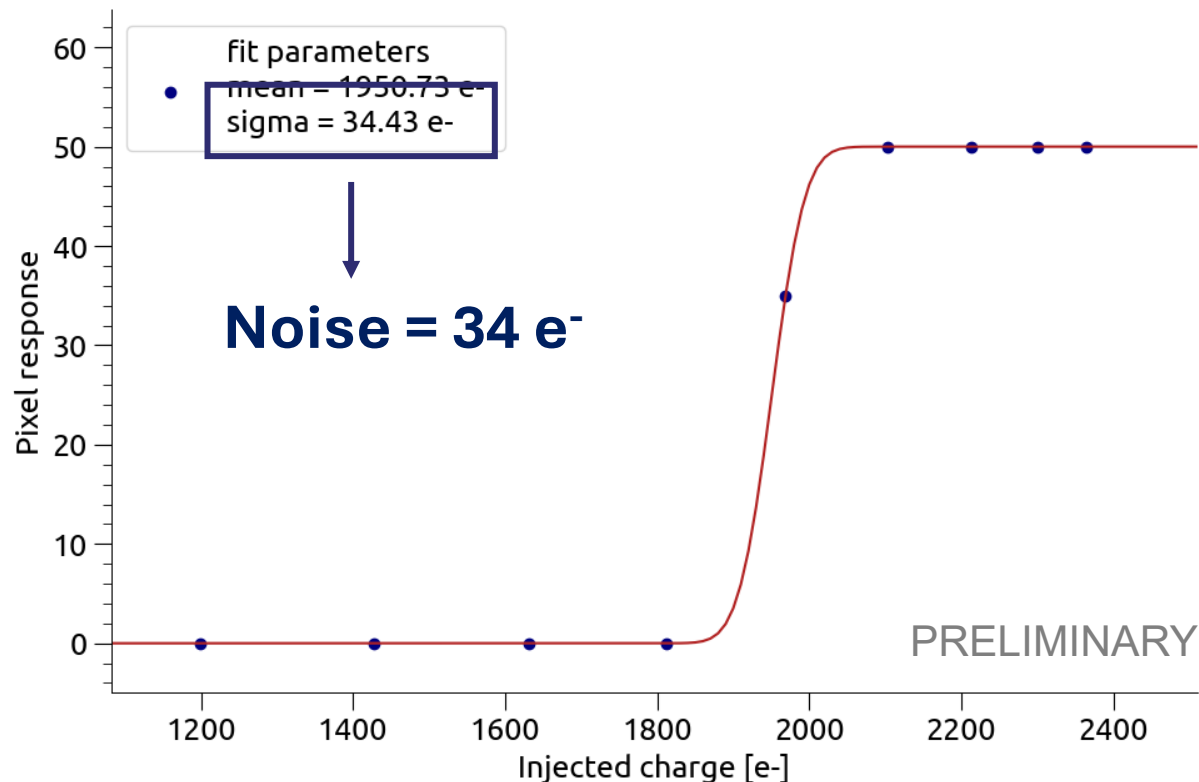


$$N(t) = N_0 \left[1 + \frac{C_s}{\sigma} (t_0 - t) \right] \left[1 + \text{erf} \left(\frac{t_0 - t}{\sqrt{2}\sigma} \right) \right]$$

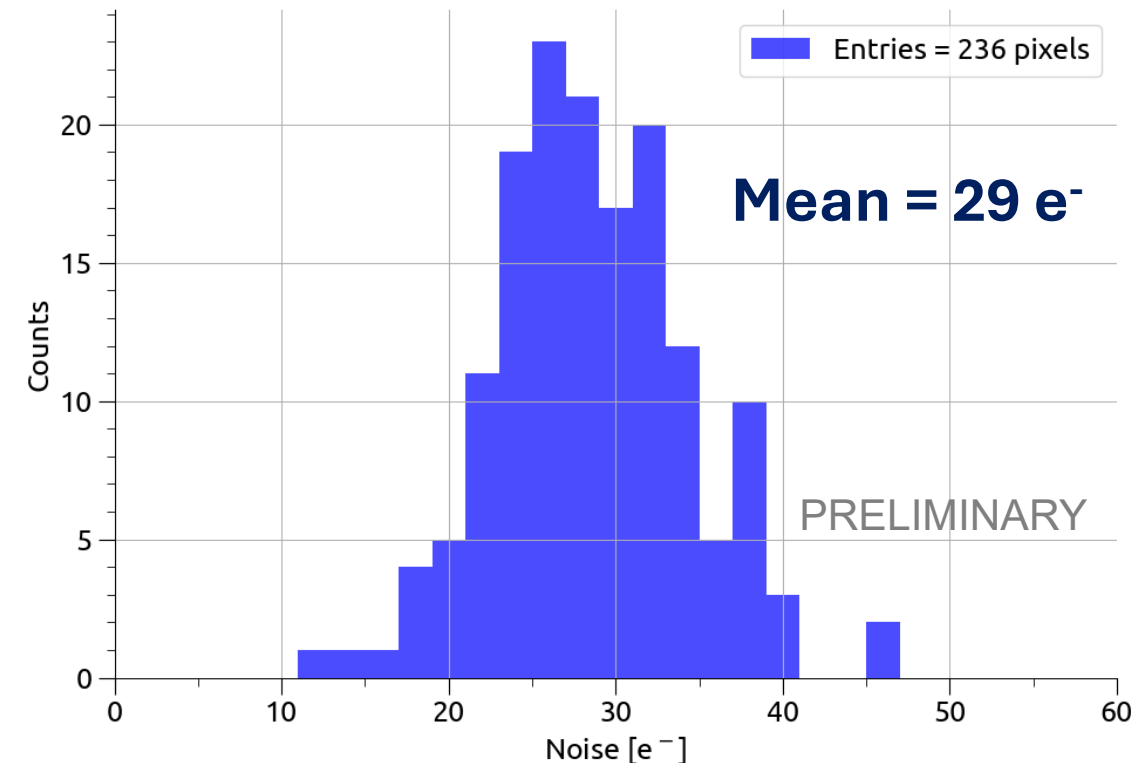
MD3 characterization: noise

Thanks to fluorescence results it is possible to calibrate the charge injected with test pulses pixel by pixel. Noise from single pixel is obtained as the sigma of the s-curve

s-curve for single pixel @ thr = 58 [DAC]



Noise distribution for the 16 × 16 sub-array



Results by Fermilab team :

T. Zenger, A. Apresyan, N. Bacchetta,
L. Bolla, A. Hayrapetyan, N. Salvador, I. Zoi

Goal:

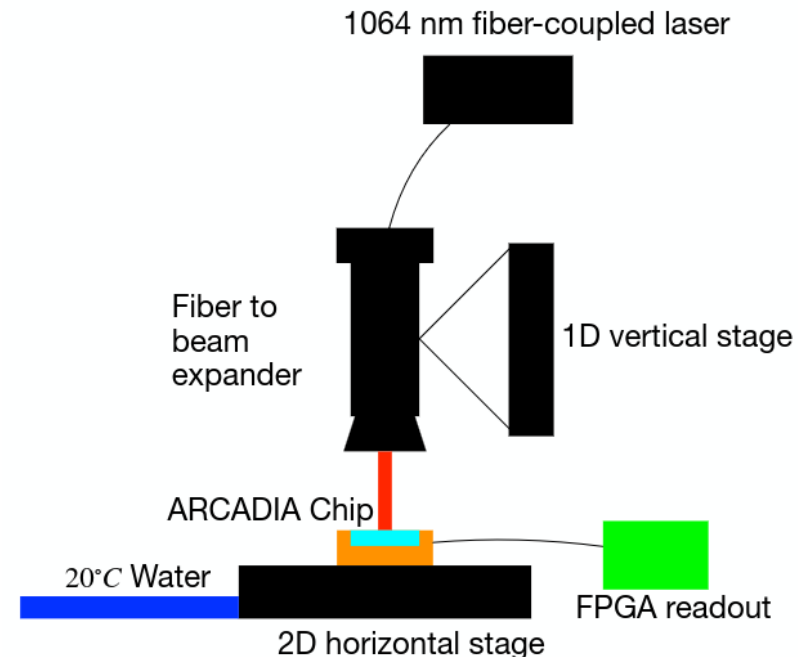
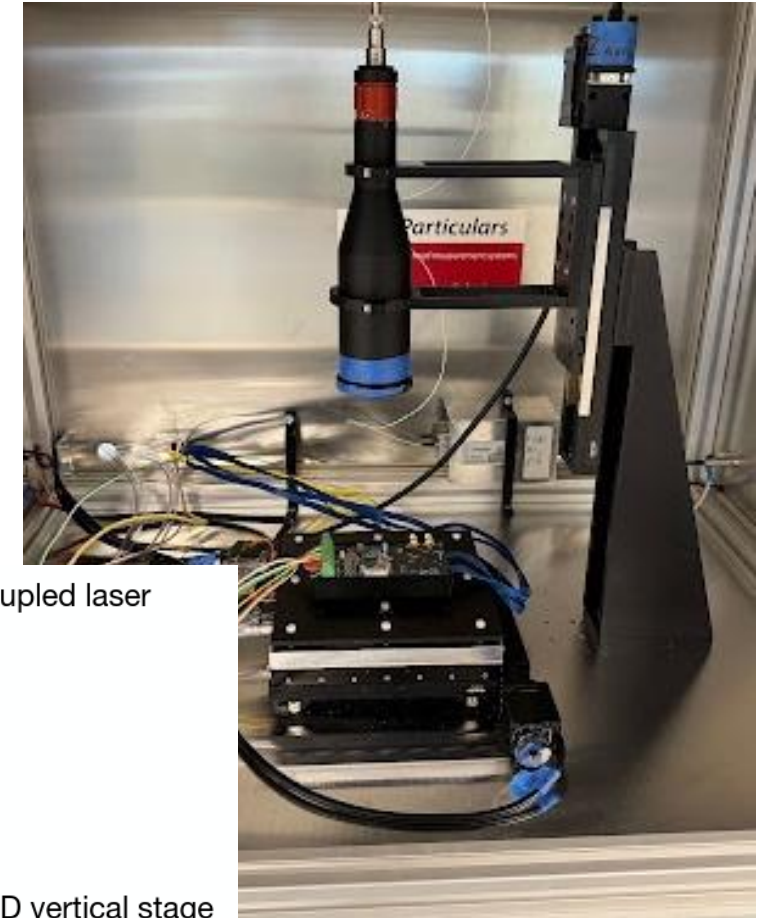
- In-pixel efficiency map
- Efficiency uniformity over a 10 x 6 pixel array

Setup:

- 1kHz micro-focused IR laser (1064 nm)
- 2D horizontal stage: 5x5 in-pixel steps (5 μm)
- Temperature controlled environment

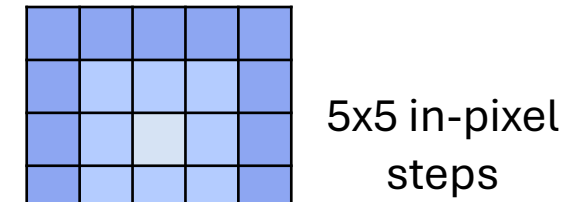
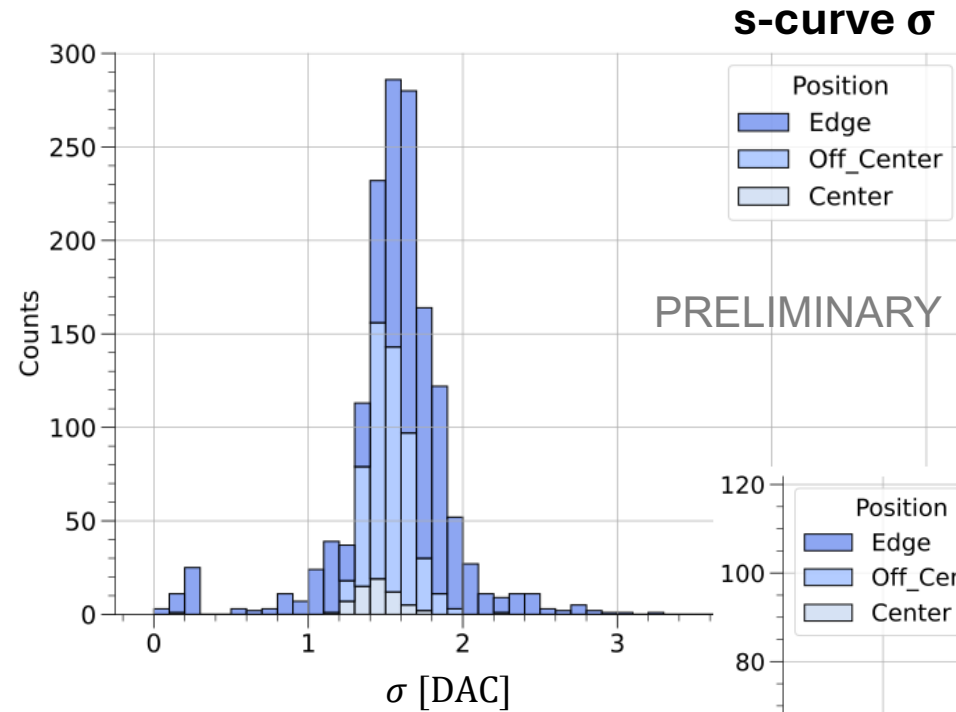
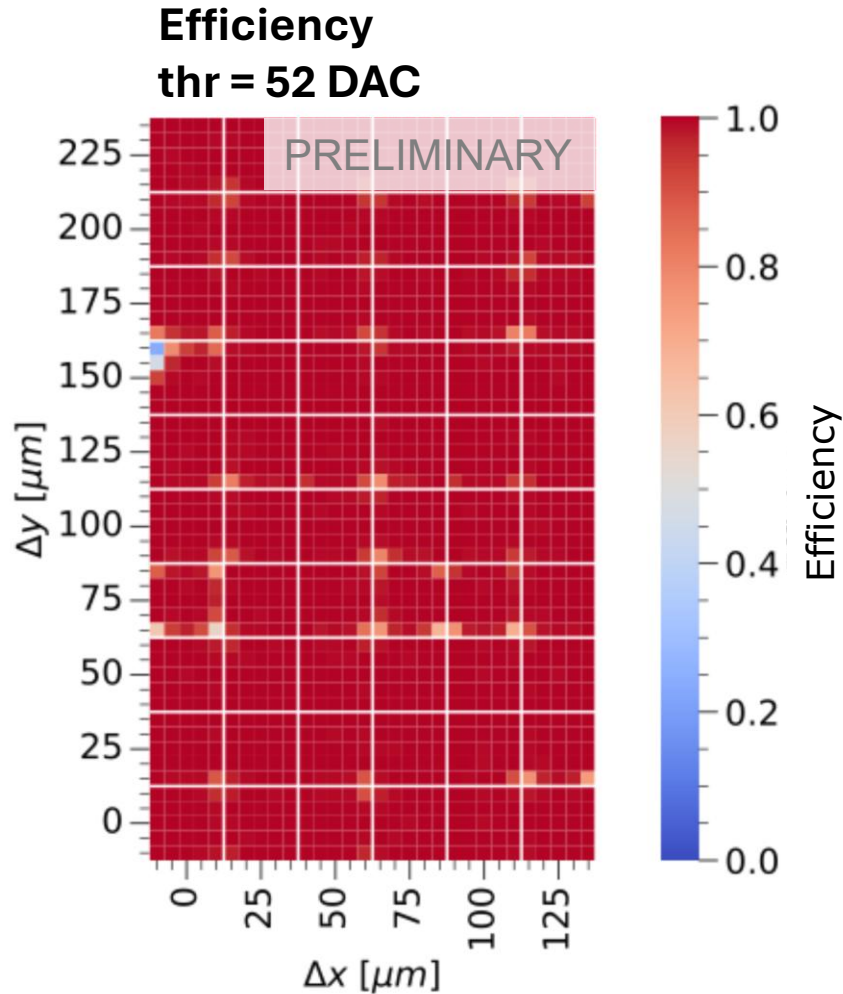
Measurements:

- In-pixel efficiency map at fixed threshold
- Threshold scan to reconstruct s-curve



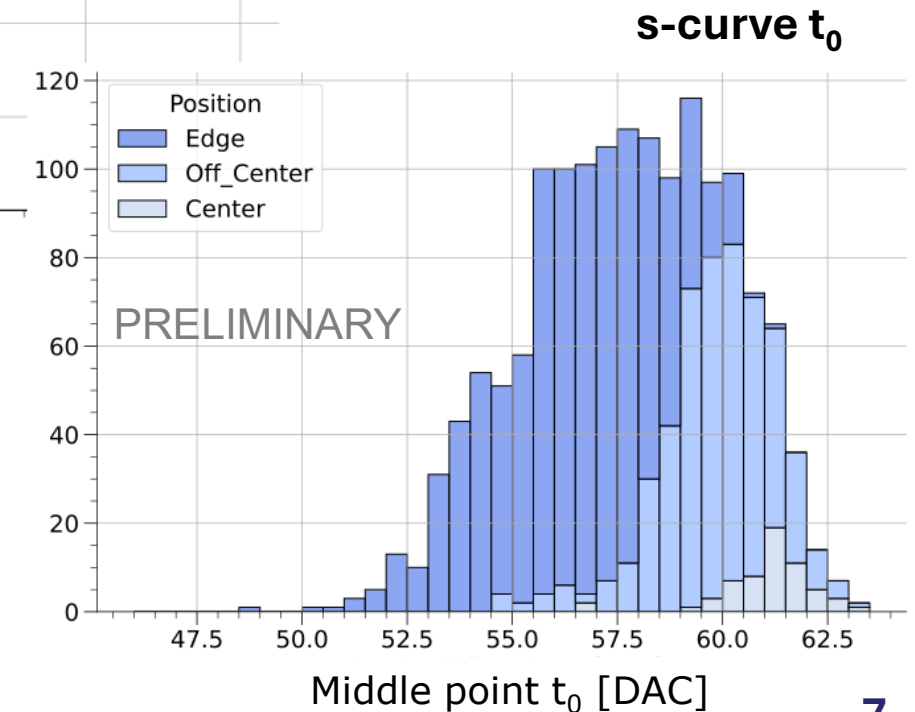
MD3 characterization: laser

Results by Fermilab team:
T. Zenger, A. Apresyan, N. Bacchetta,
L. Bolla, A. Hayrapetyan, N. Salvador, I. Zoi



σ : width of s-curve

Middle point t_0 : threshold value corresponding to 50% efficiency



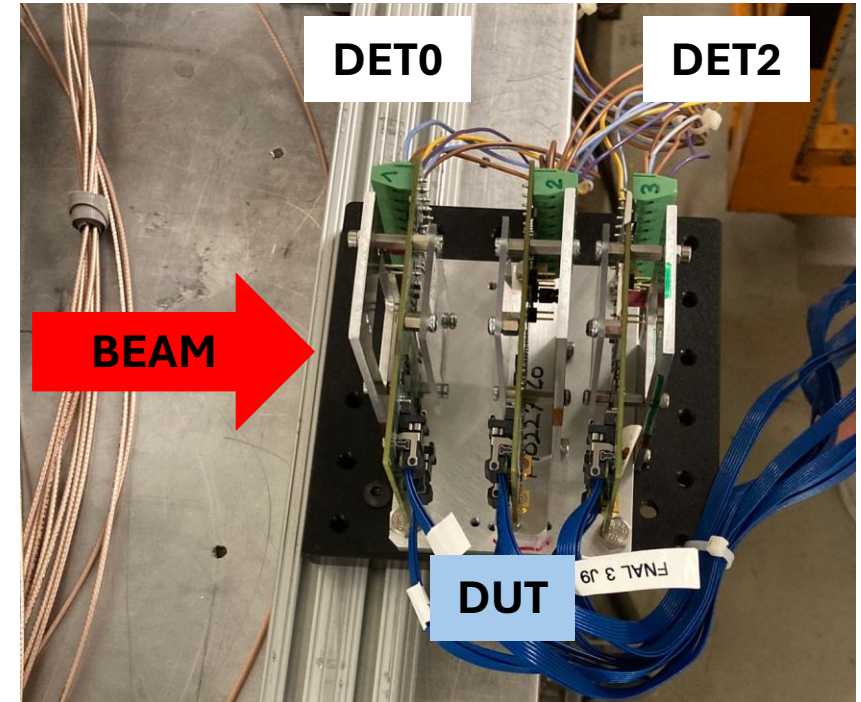
Test beam measurements done at **Fermilab Test Beam Facility (FNAL FTBF)** in Summer 2024 with a **120 GeV proton beam**.

Measurements performed:

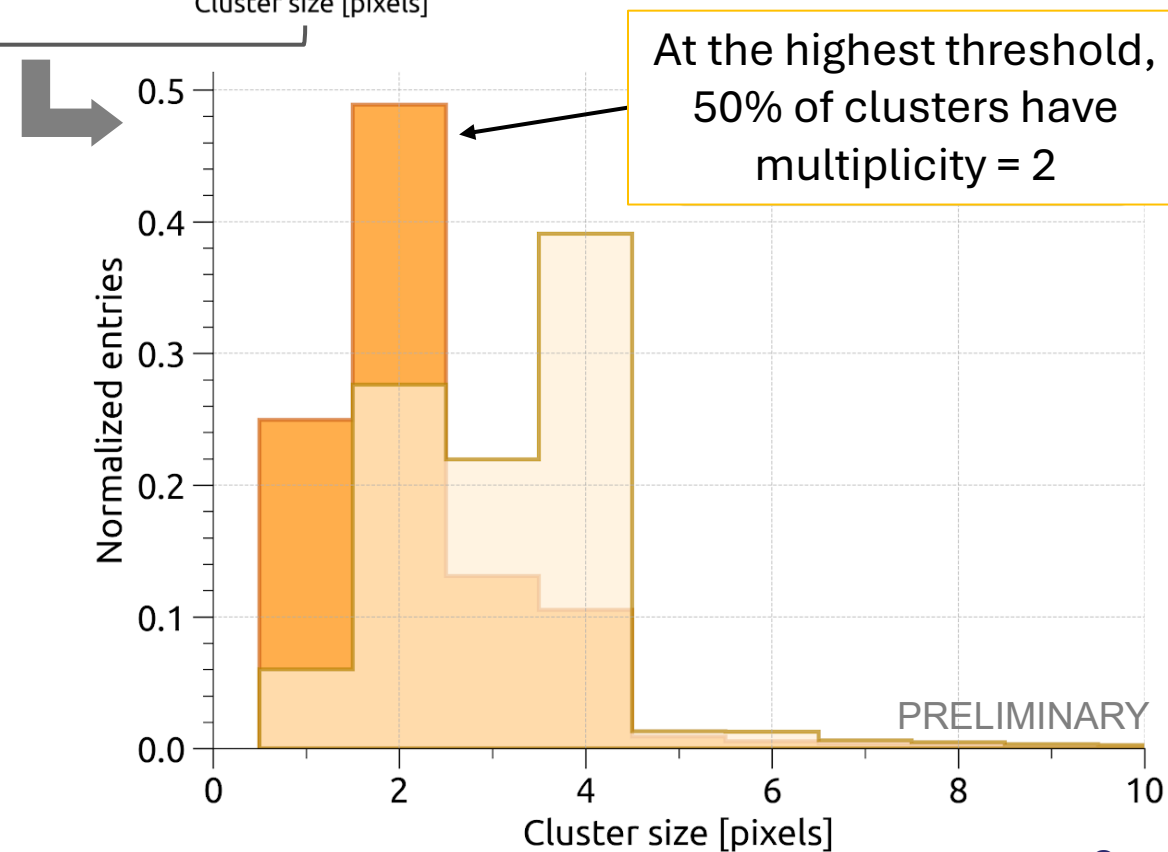
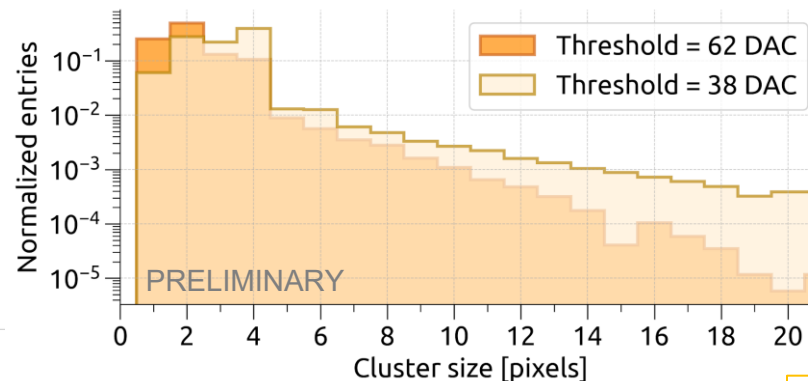
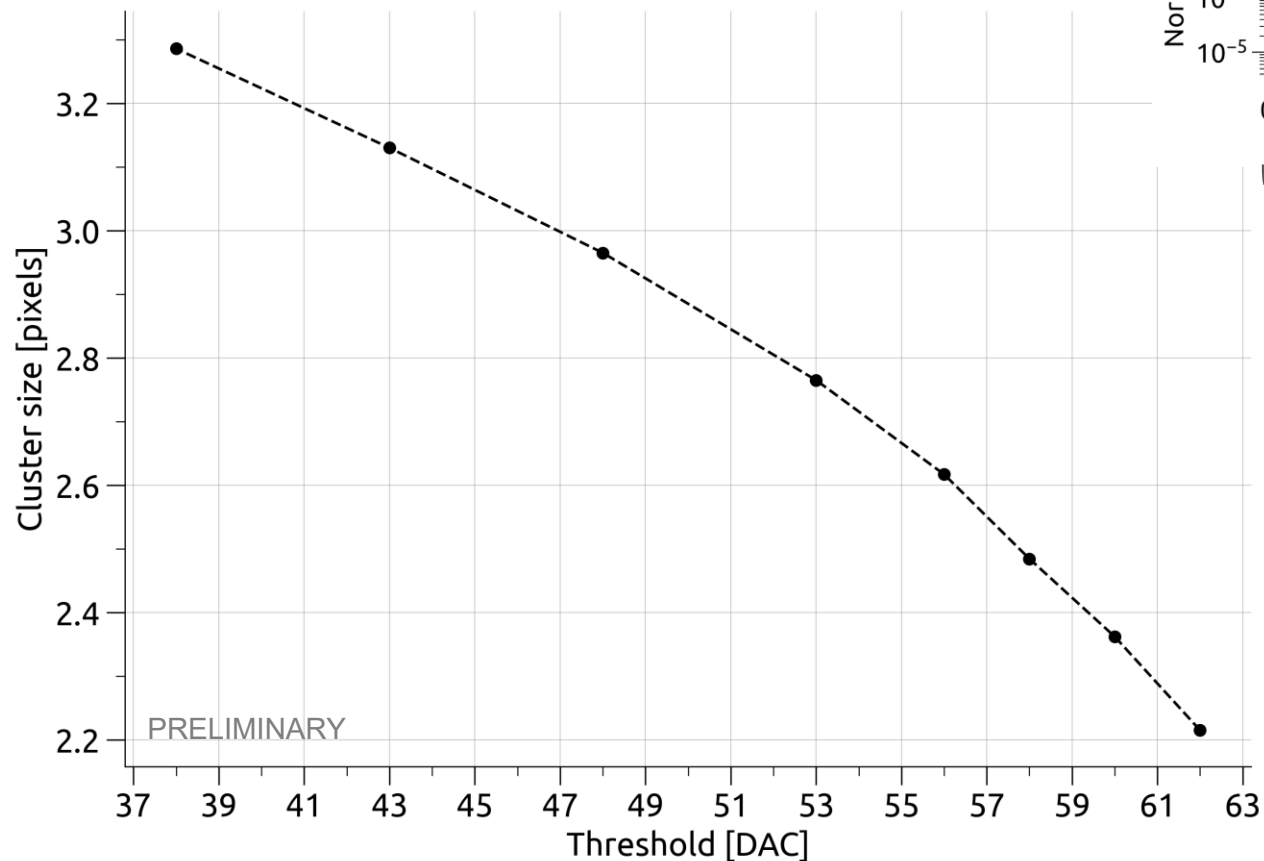
- Threshold scan
- Scan on FE parameters
- Depletion voltage scan
- Threshold scan with tilted DUT

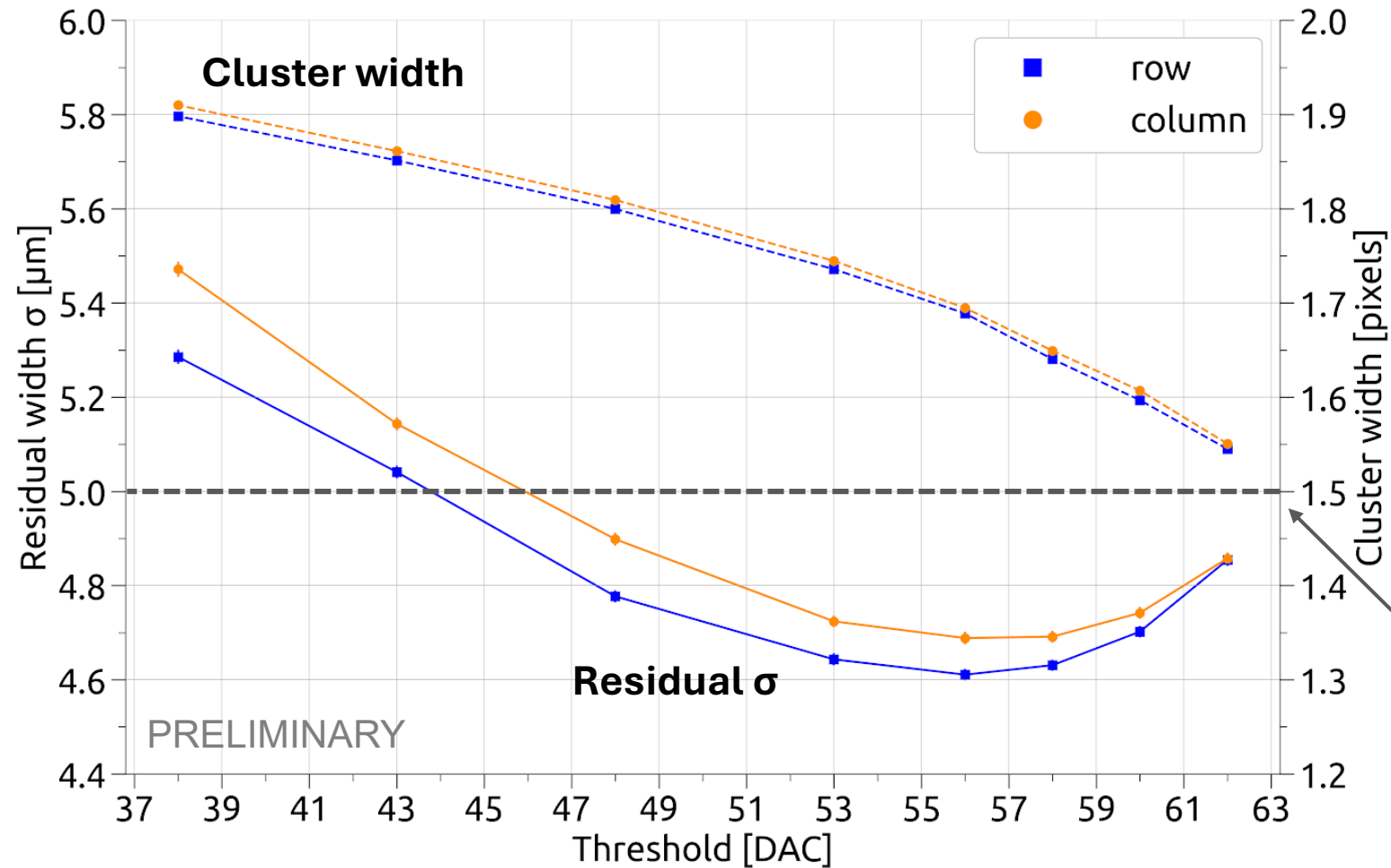
Experimental setup:

- Two ARCADIA MD3 (200 μm thick) as tracking planes
- One ARCADIA MD3 (200 μm thick) as Device Under Test
- DAQ: Triggerless acquisition with timestamp synchronization



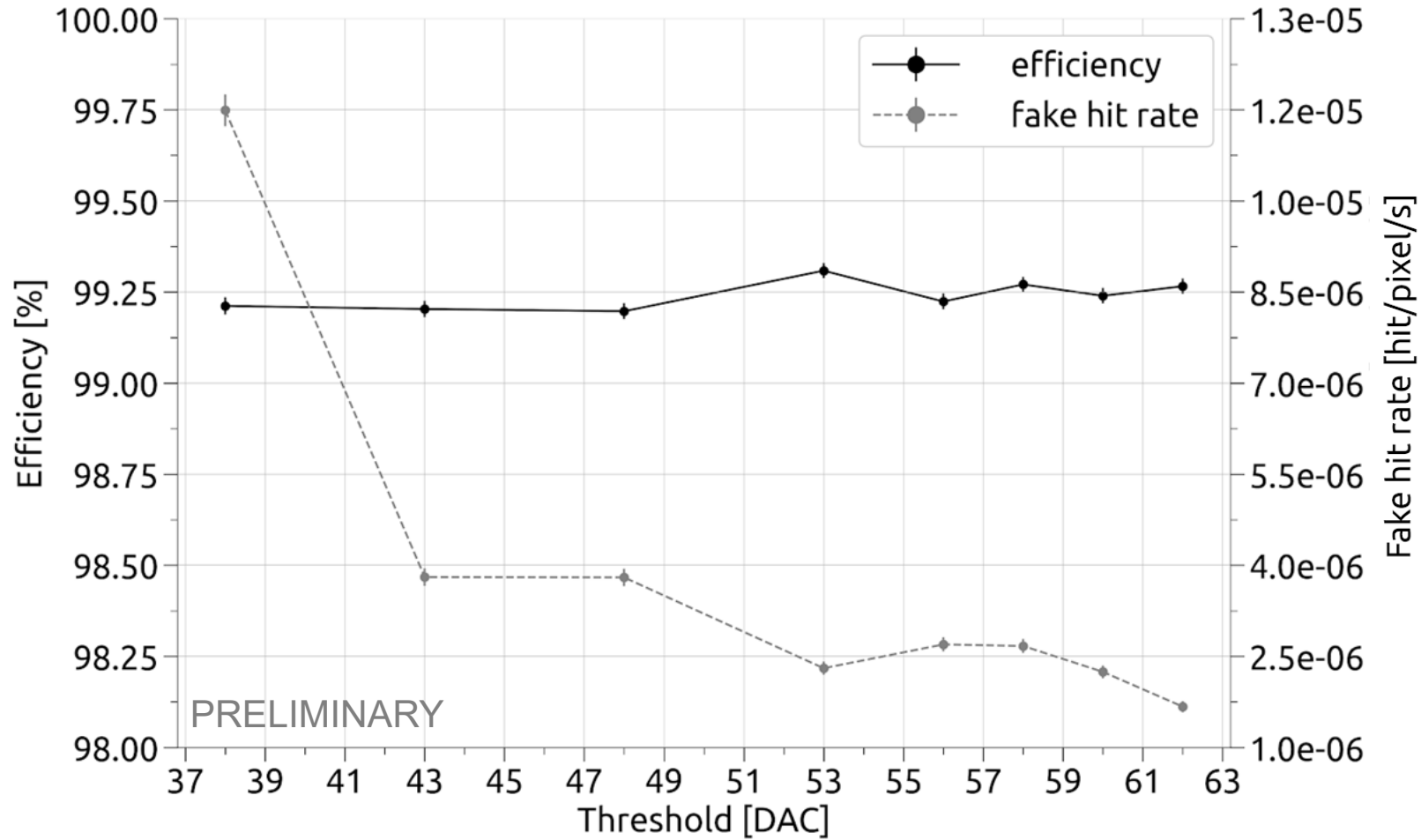
DUT clusters associated to tracks



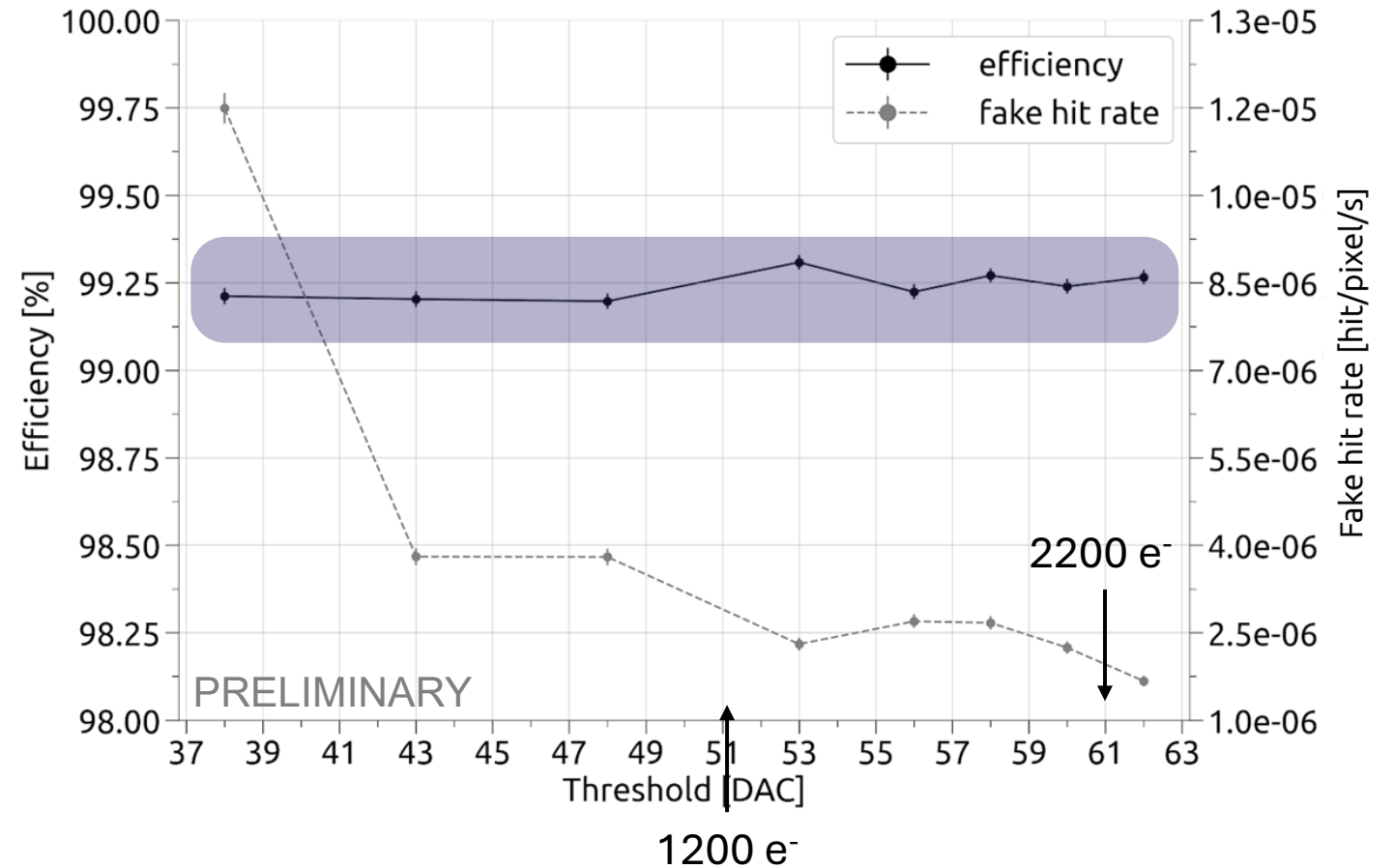
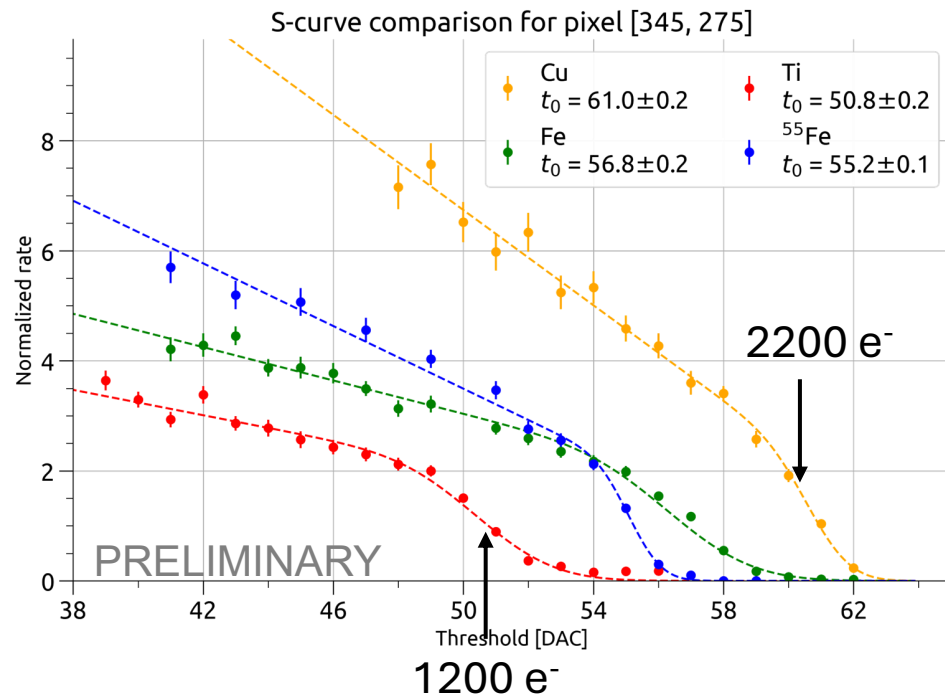


Cluster width always greater than 1.5 pixels

Residual width always below the **binary resolution** (7.2 μm)



Fake hit rate measured
during no-beam time
12 masked pixels on the DUT



Maximum threshold value corresponds roughly to **2200 electrons** (calibrated via fluorescence measurements).

In 200- μm thickness, a MIP releases $\sim 16000 \text{ e}^- \rightarrow$ the highest available threshold corresponds to a much lower charge released.

- **Lab characterization** of ARCADIA: **threshold calibration** and **efficiency uniformity** studies
- **First in-beam characterization** of the ARCADIA chip
- Thick active region and low threshold range → **strong effect of charge sharing**
- **Spatial resolution:** the minimum width of the residual distribution of **4.6 μm** with a 1D average cluster width of about 1.6 pixels
- **Efficiency** always **above 99%**

Future developments:

- **Characterization paper** ready for submission and **test beam paper coming** next
- **Additional test beam campaign** with an **extended telescope** to improve track reconstruction and validate these first results
- Comparison of performances for DUTs with **different active thicknesses**
- Measurements with **low-energy electron beam**
- Specific measurements on **power consumption for space** application

- Lab characterization
- First in-beam charac
- Thick active region an
- **Spatial resolution:** t
- cluster width of about
- **Efficiency** always ab

Future developments:

- **Characterization pa**
- **Additional test beam**
- validate these first re
- Comparison of perfor
- Measurements with L
- Specific measurements on power consumption for space application



Padova team

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ng next
track reconstruction and

Thank you for your attention



Backup

ARCADIA wafer

Timing application

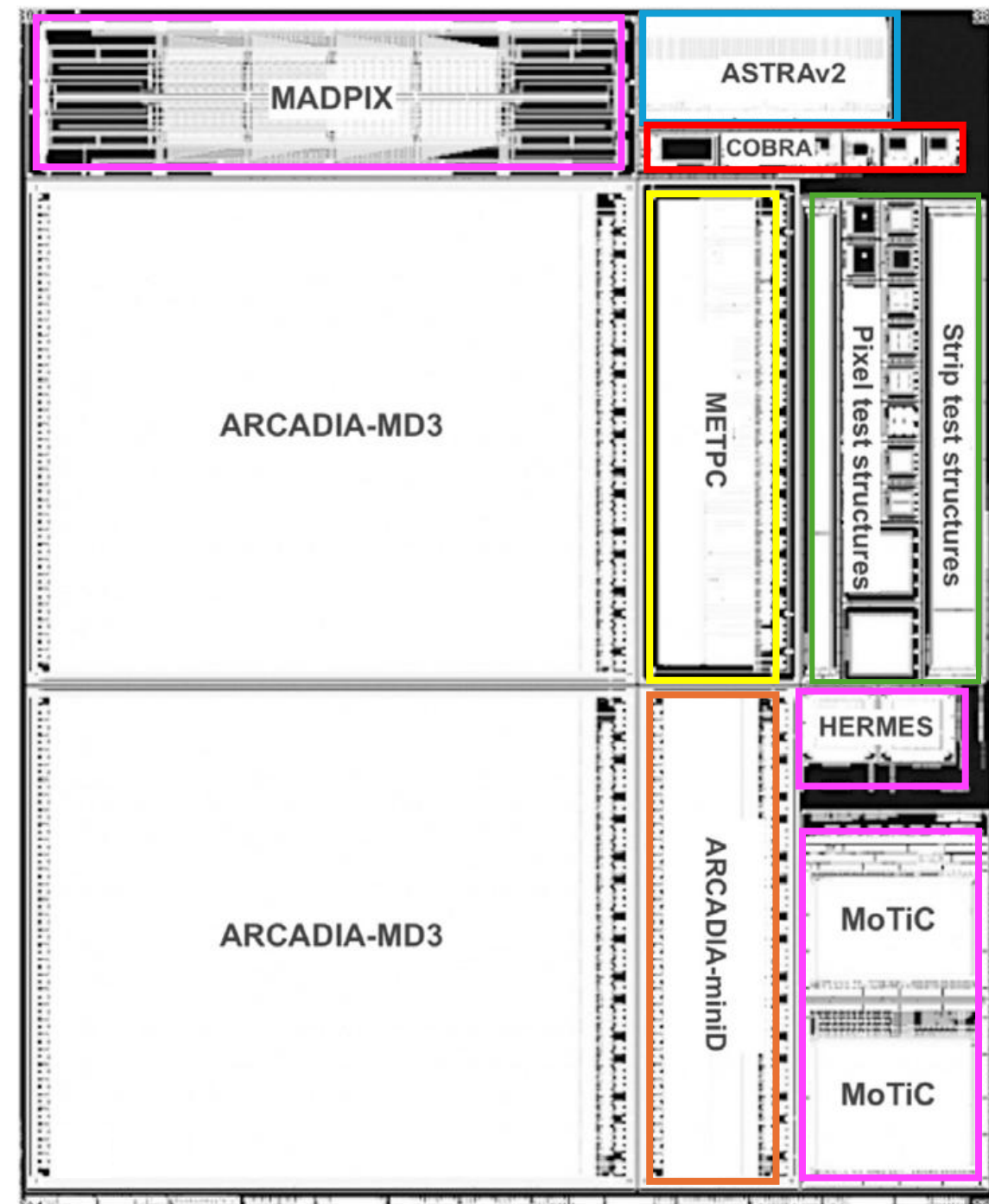
Passive structures for
electrical characterization

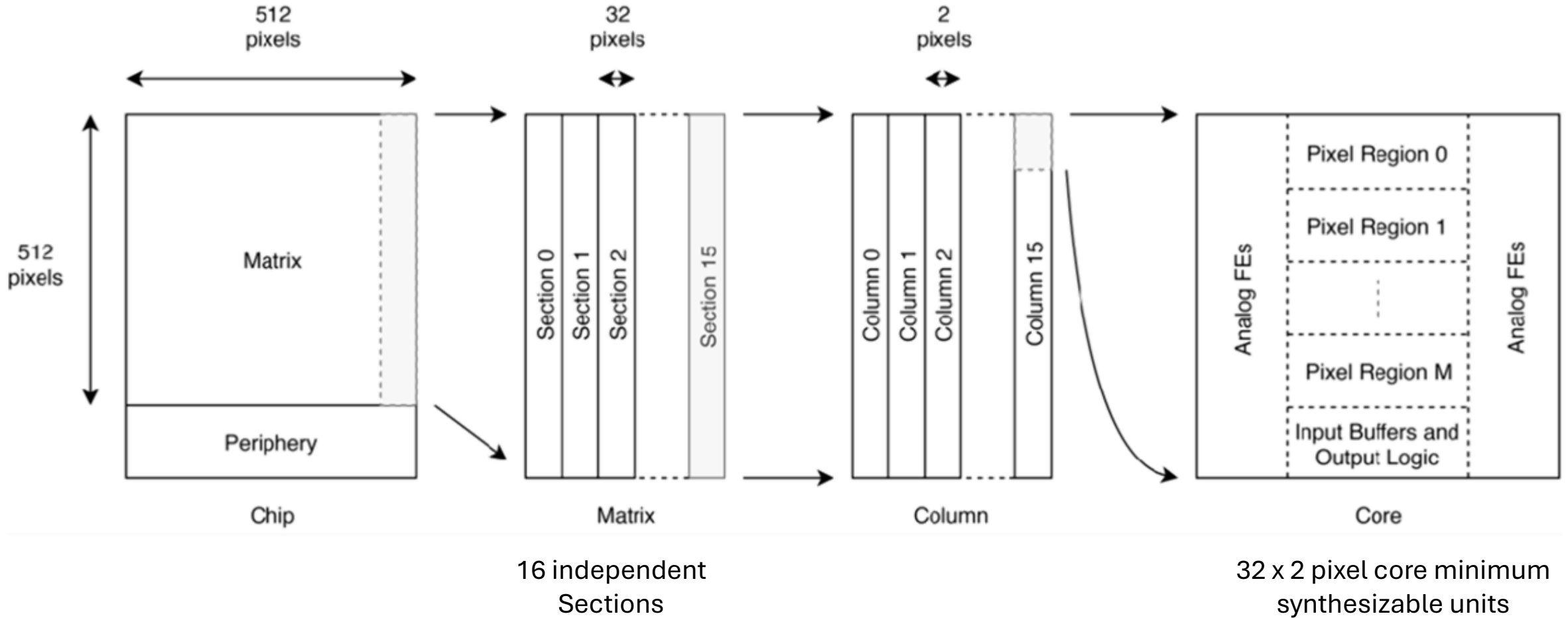
X-ray application (multi
photon counter)

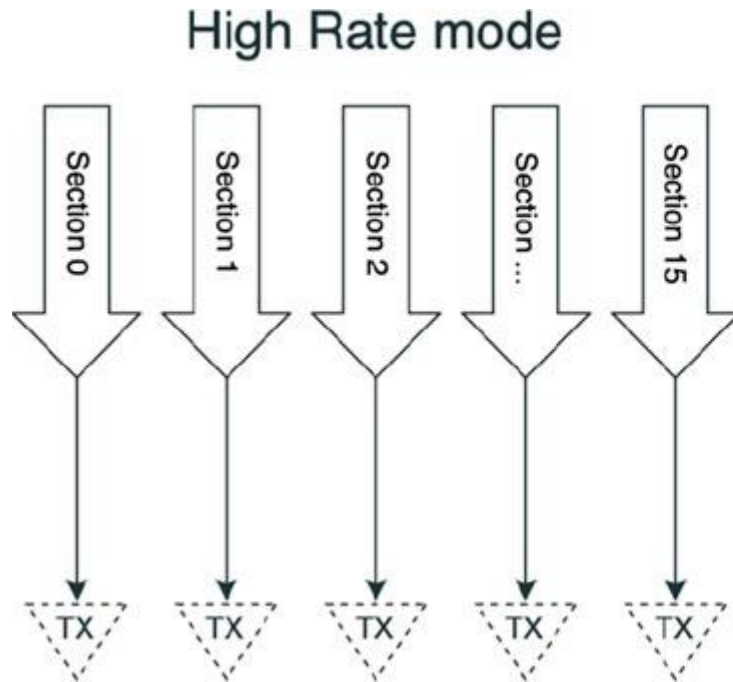
Debugging implemented
power management IPs

Space-borne applications

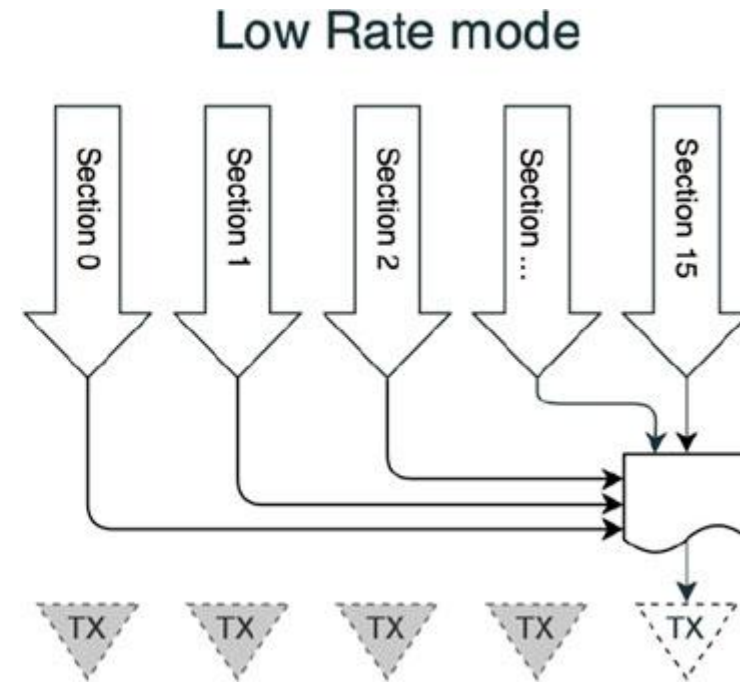
Tracking and dosimetry







Designed to sustain particle rate
of 100 MHz/cm^2

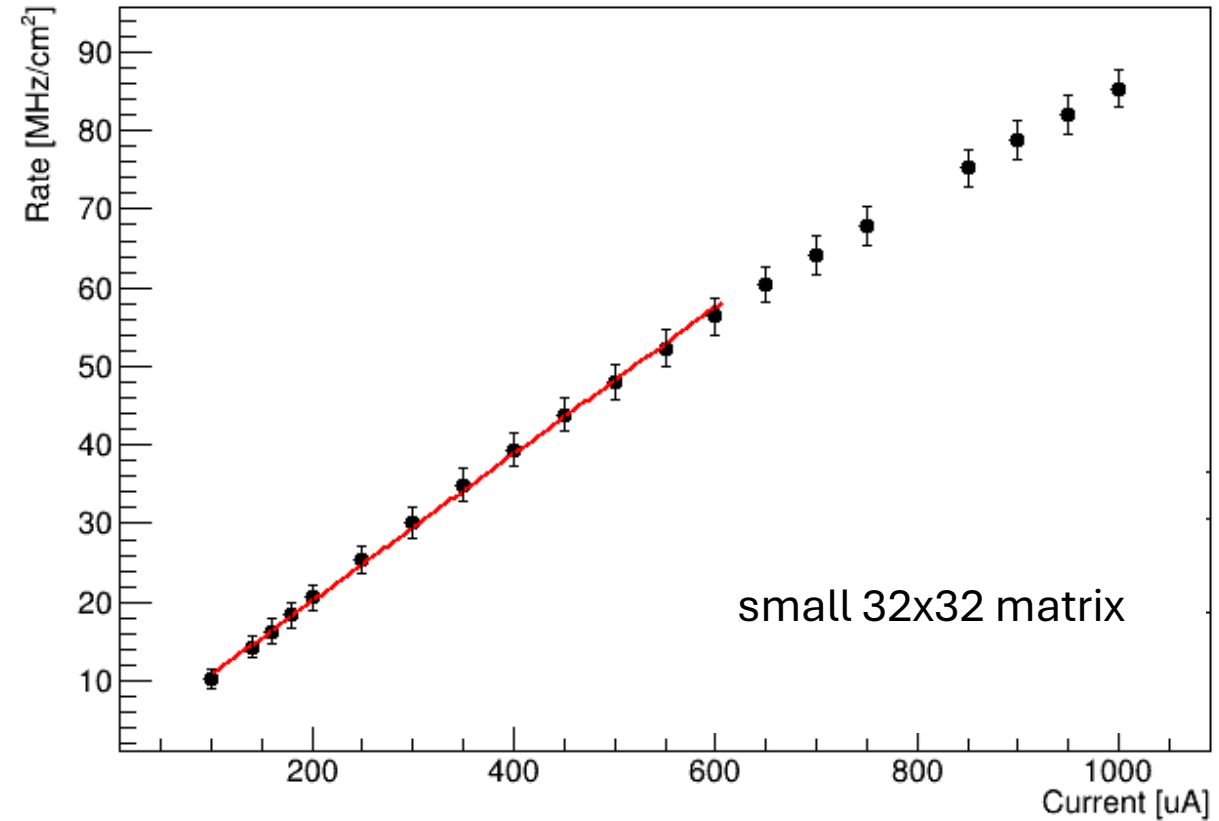
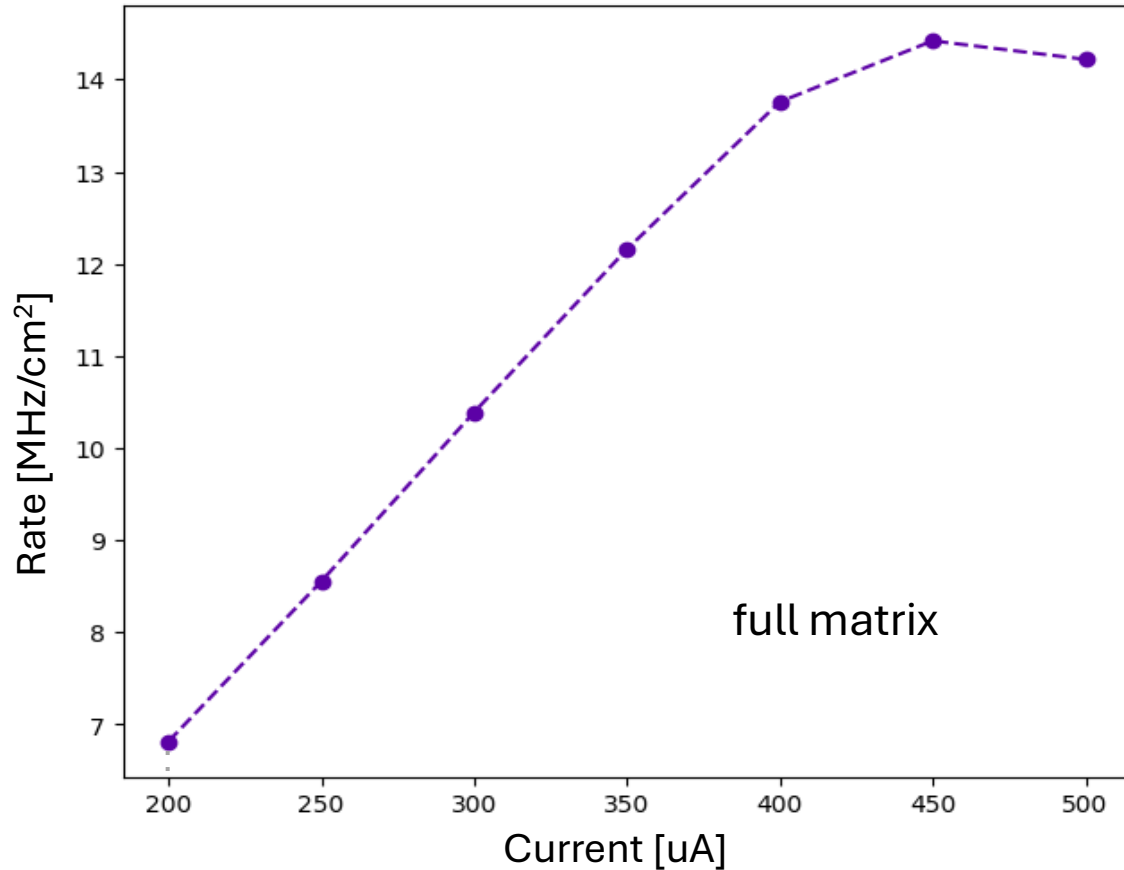


For low-rate applications:
Data from all section readout units are buffered into
a central FIFO and only one transceiver is enabled.

Power consumption: $\sim 10 \text{ mW/cm}^2$

MD3 characterization: rate evaluation

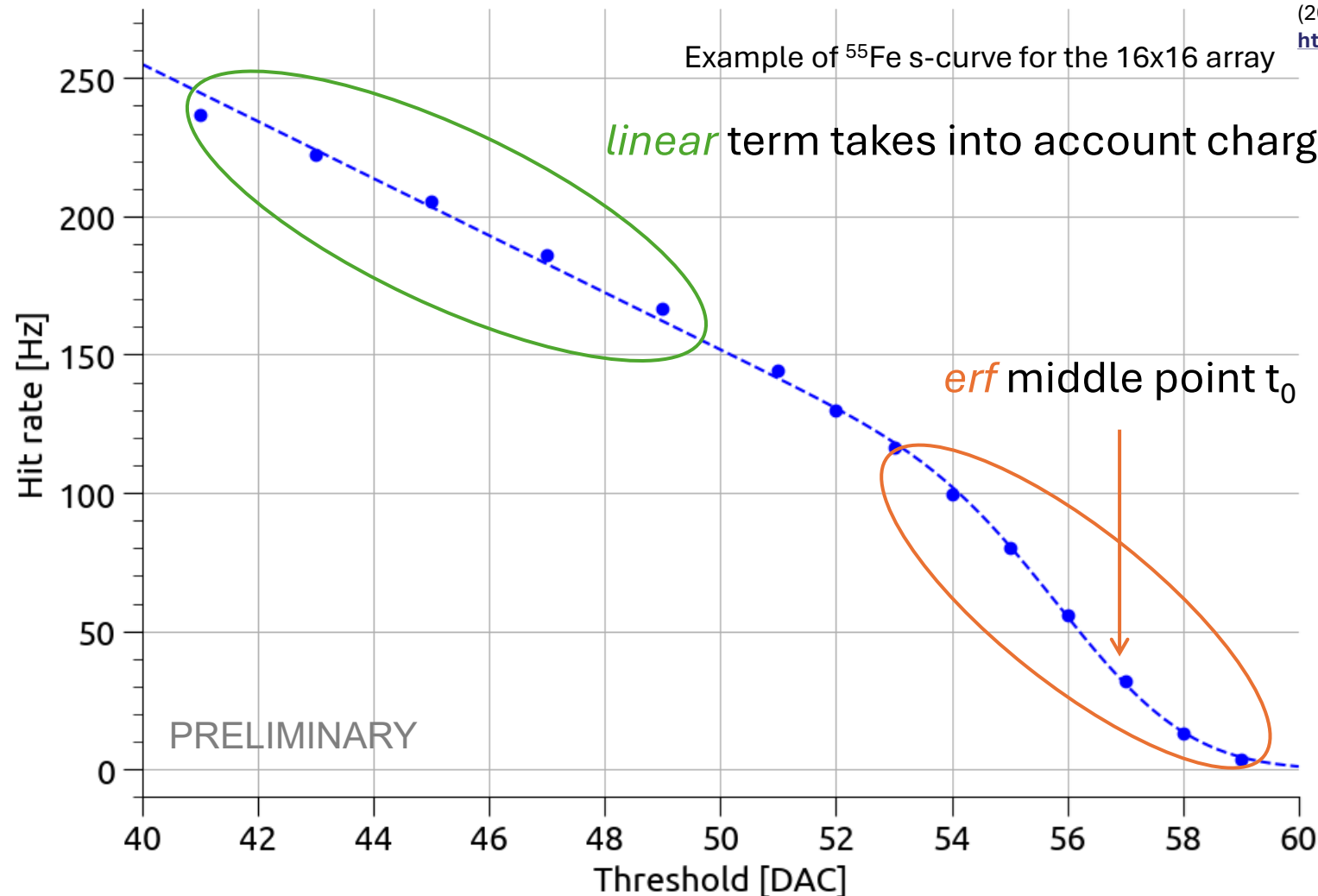
Rate response is evaluated as function of the current of the X-ray tube.
Results for cluster rate @80kV X-ray tube voltage.



Hit rate vs threshold: the electronic cloud released by X-ray diffuses in silicon leading to **charge sharing**, therefore the fit model is modified with respect to test pulse s-curve.

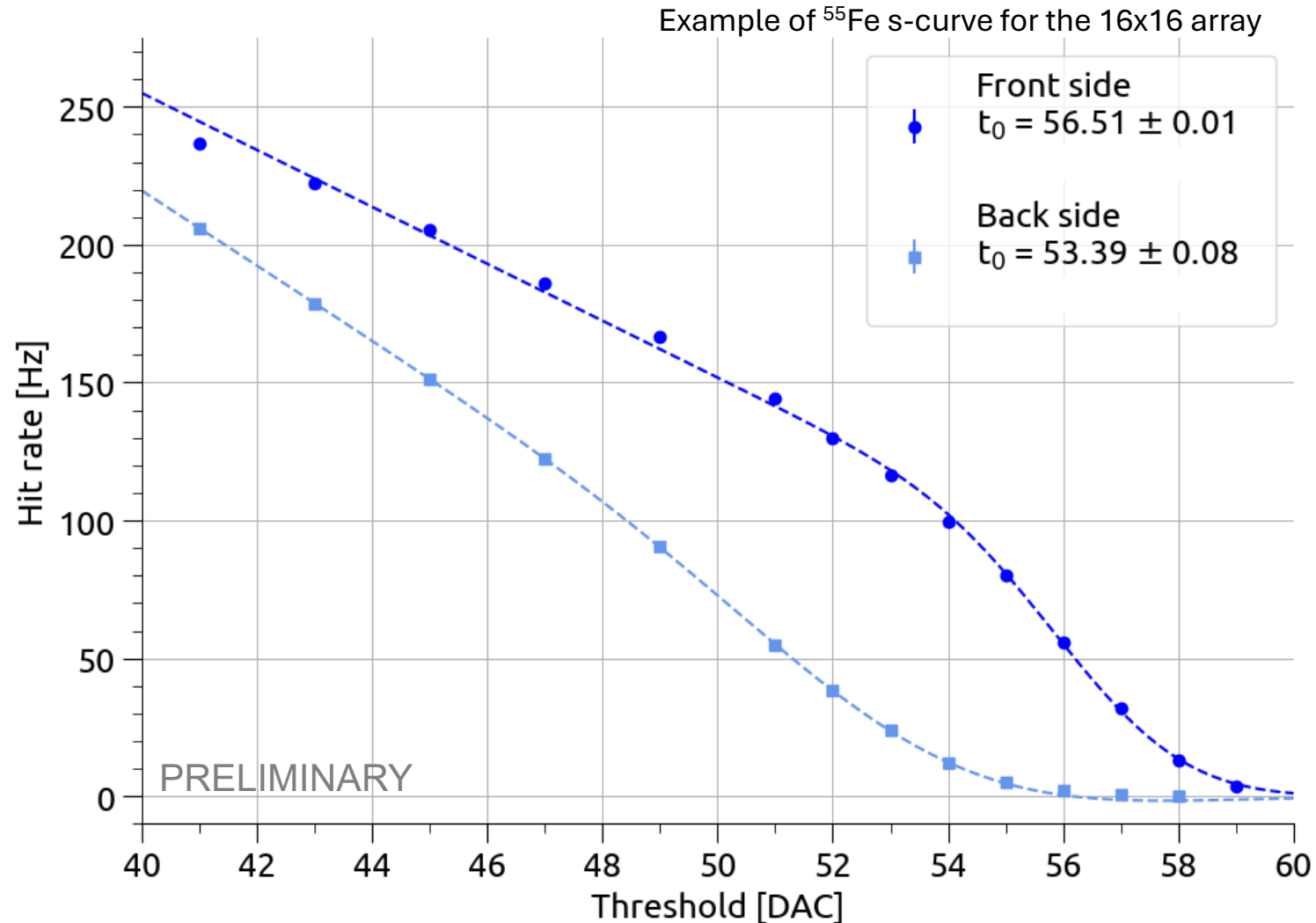
Kraft, P., et al. "Performance of single-photon-counting PILATUS detector modules." *Synchrotron Radiation* 16.3 (2009): 368-375.

<https://doi.org/10.1107/S0909049509009911>



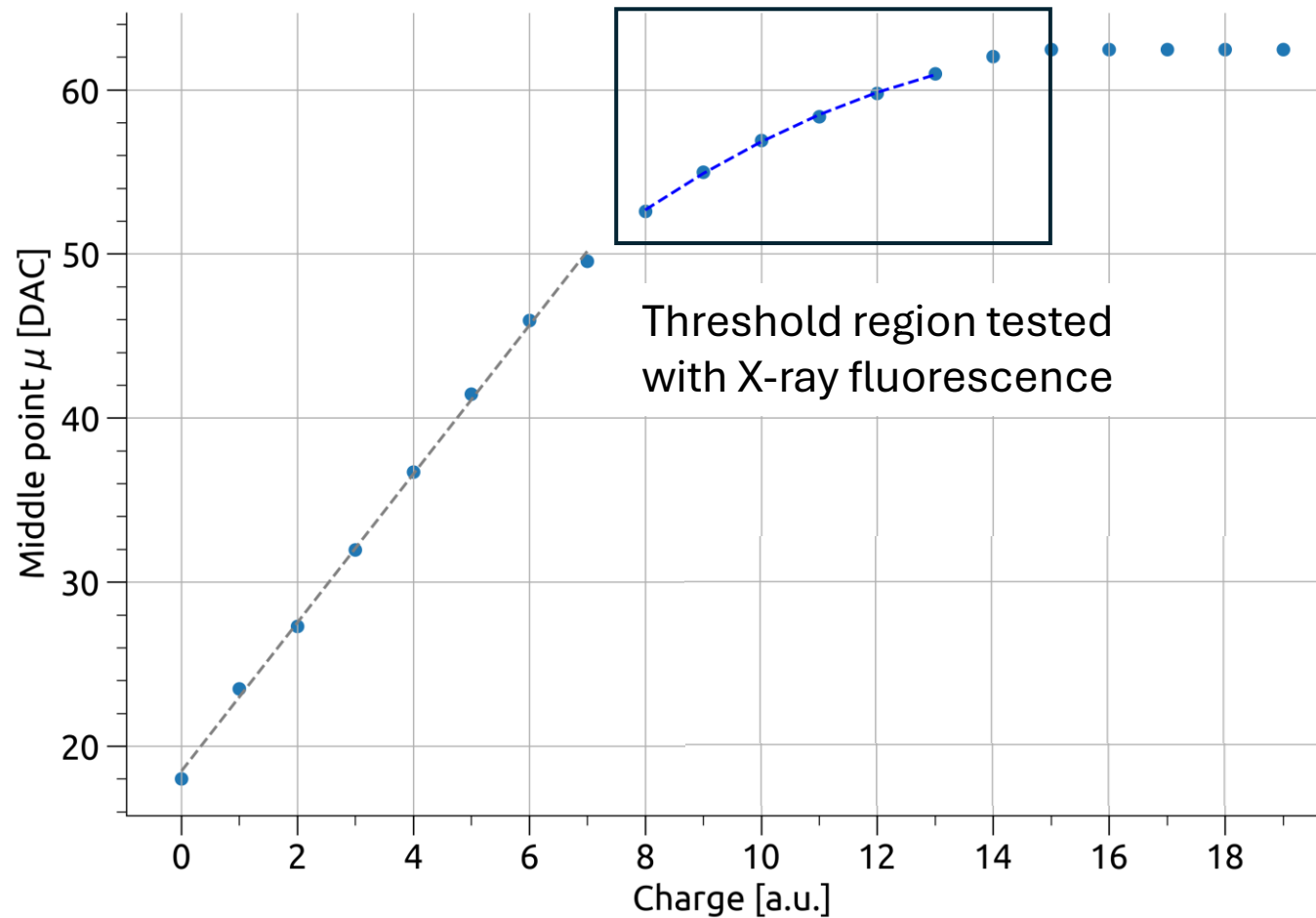
MD3 characterization: front-back measurements

The electronic cloud released by X-ray diffuses in silicon leading to charge sharing.
More charge sharing when illuminating from the back side

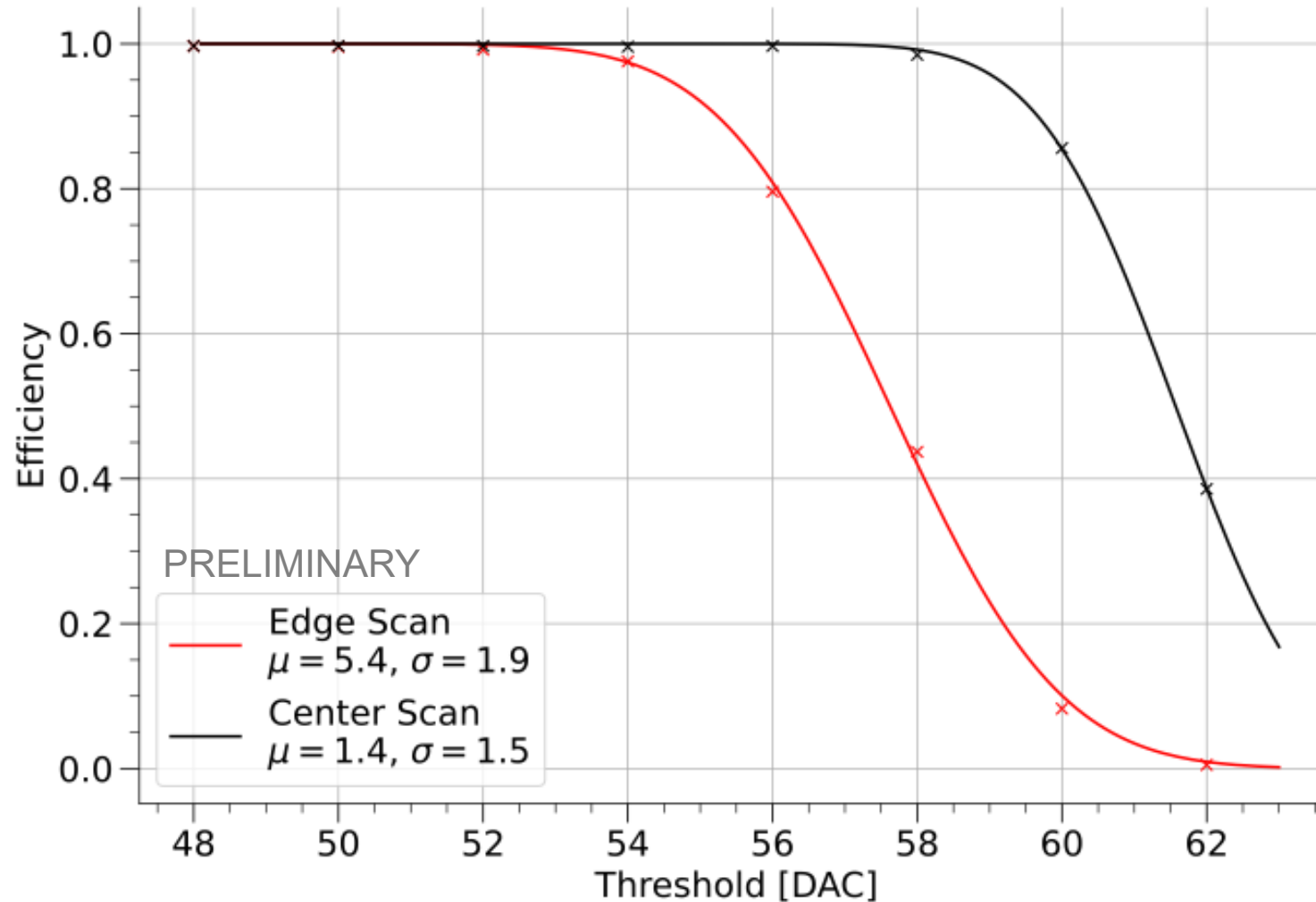


MD3 characterization: injection charge calibration

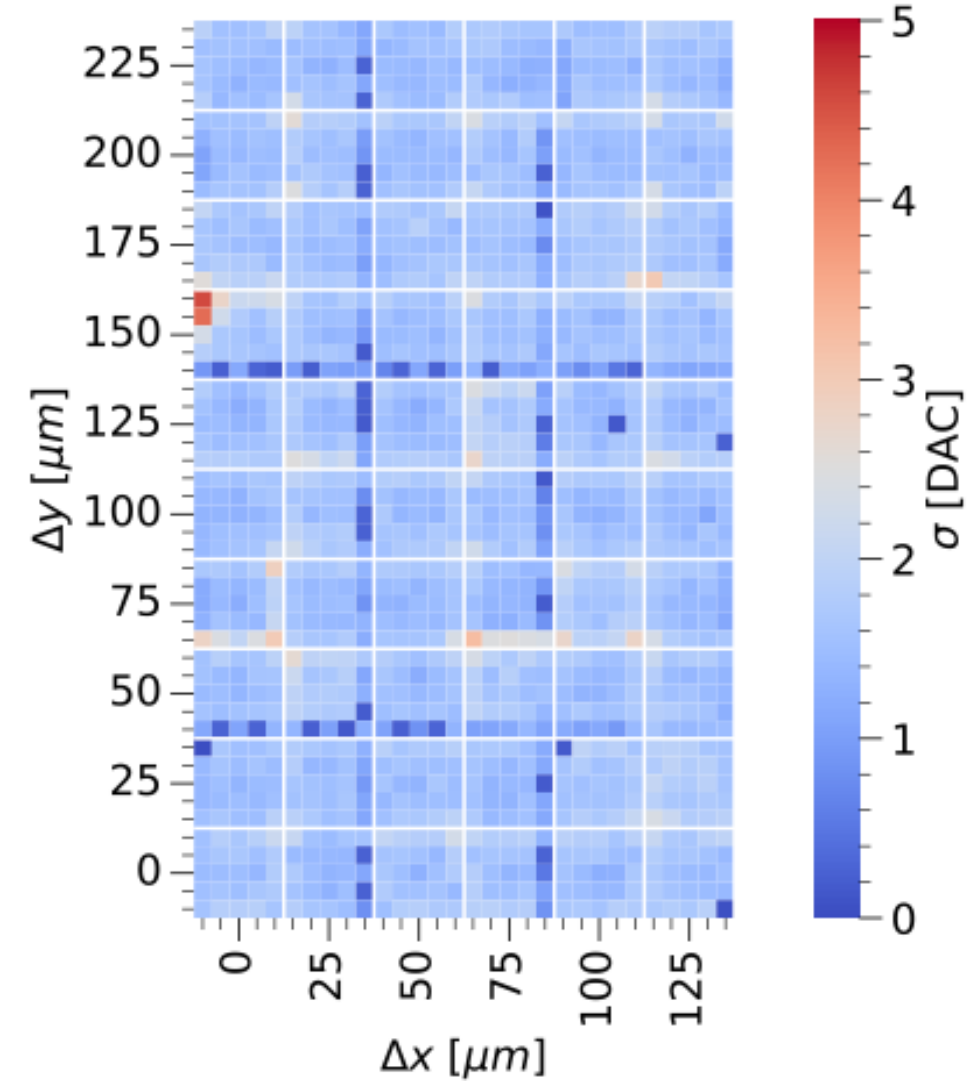
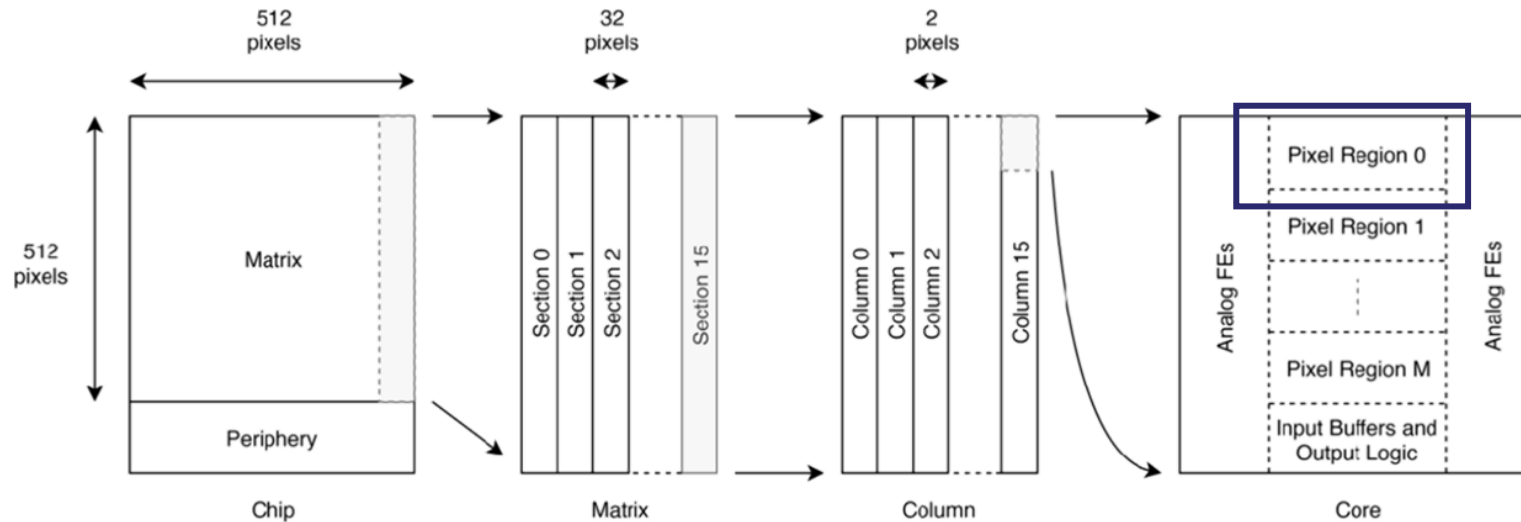
Middle point of the s-curve as a function of the injected charge in arbitrary units for a single pixel. There are clearly two regimes, at some point the linearity is lost



Example of in-pixel efficiency s-curve with IR laser illumination



Very low values of σ correspond to the edges of the 4x2 pixel region.





Data are analysed spill-by-spill using the **Corryvreckan** software.

Analysis steps:

- **Clusterization**
- **Prealignment** of the three planes from correlation plots
- **Alignment** of the DUT with DUT residual distribution
- **Tracking** with the two external planes and **DUT association**
- Analysis of the **residual** distribution and **efficiency**
Association window: 5 μ s and 500 μ m
Edge cut: 30 pixels on both row and column axis

D. Dannheim, et AL, “Corryvreckan: a modular 4D track reconstruction and analysis software for test beam data,” *Journal of Instrumentation*, vol. 16, no. 03, p. P03008, Mar. 2021. [doi:10.1088/1748-0221/16/03/P03008](https://doi.org/10.1088/1748-0221/16/03/P03008)

